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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION of

Norio Hirashita et al.

Group Art Unit: 2823

Serial No.: 09/825,973

Examiner: M. Estrada

Filed: April 5, 2001

For: A STRUCTURE OF A FIELD EFFECT TRANSISTOR HAVING METALLIC SILICIDE AND MANUFACTURING METHOD THEREOF

RESPONSE TO RESTRICTION REQUIREMENT AND AMENDMENT

Honorable Assistant Commissioner for Patents
Washington, D.C. 20231

Date: September 27, 2002

Sir:

In response to the Restriction Requirement dated August 28, 2002, the following election, amendments and remarks are respectfully submitted in connection with the above-identified application.

In the Abstract:

Please cancel the Abstract and replace with the Abstract attached herewith.

In the Specification:

Replace the paragraph beginning on page 4, line 6 with the following paragraph:

"In order to achieve the above object, in a field effect transistor having metallic silicide layers composed of refractory metal and silicon, the bottom surfaces of the